



DMP4025LK3

40V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(on)} max	I _D max T _A = +25°C (Note 6)
-40V	25mΩ @ V _{GS} = -10V	-8.6A
-40V	45mΩ @ V _{GS} = -4.5V	-7.0A

Description

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor control
- Backlighting
- DC-DC Converters
- Printer equipment

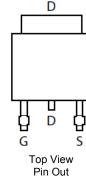
Features

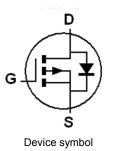
- Low On-Resistance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead-Free Finish; RoHS compliant (Note 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See diagram below
- Terminals: Finish Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208 ⁽³⁾
- Weight: 0.315 grams (approximate)







Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DMP4025LK3-13	P4025L	13	16	2,500

Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



D'' = Manufacturer's Marking
P4025L = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 10 = 2010)
WW = Week (01 - 53)



Maximum Ratings (@T_A = +25°C unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	-40	V
Gate-Source Voltage			V _{GSS}	±20	
		(Notes 6)		-8.6	
Continuous Drain Current	V _{GS} = -10V	T _A = +70°C (Notes 6)	ID	-6.9	
		(Notes 5)	1	-6.7	
Pulsed Drain Current	V _{GS} = -10V	(Notes 7)	I _{DM}	-35	A
Continuous Source Current (Body diode)		(Notes 7)	Is	-8.6	
Pulsed Source Current (Body diode)		(Notes 7)	I _{SM}	-35	

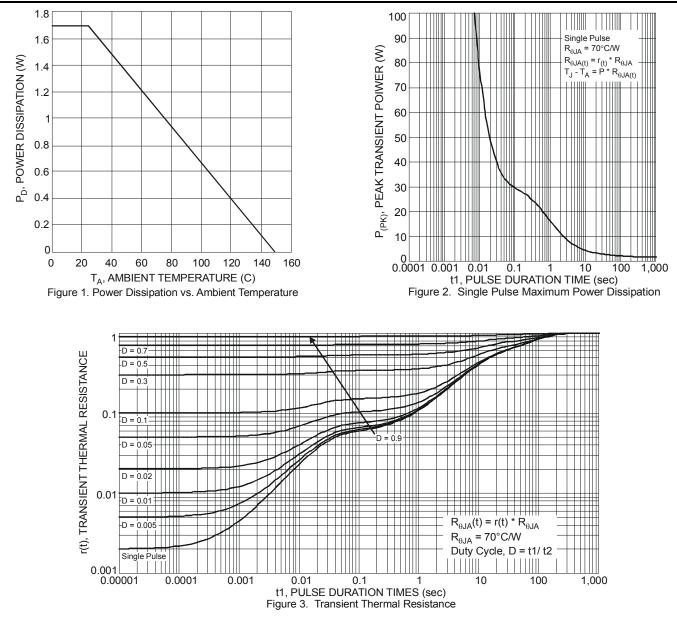
Thermal Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Dower Dissinction	(Notes 5)		1.7	14/
Power Dissipation	(Notes 6)	PD PD	2.78	W
Thermal Resistance, Junction to Ambient	(Notes 5)	D	74	
	(Notes 6)	R _{0JA}	45	00.004
Thermal Resistance, Junction to Case	(Notes 6)	R _{θJC}	7.1	°C/W
Thermal Resistance, Junction to Lead	(Notes 8)	R _{θJL}	1.43	
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

 For a device surface mounted on minimum recommended FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 Same as note (5), except the device is surface mounted on 25mm X 25mm X 1.6mm FR4 PCB.
 Repetitive rating on 25mm X 25mm FR4 PCB, D=0.02, pulse width 300µs – pulse width by maximum junction temperature.
 Thermal resistance from junction to solder-point (at the end of the drain lead). Notes:



Thermal Characteristics





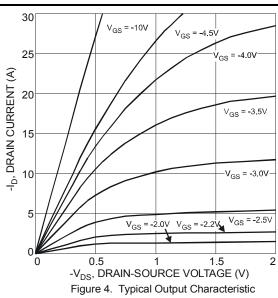
Electrical Characteristics (@T_A = +25°C unless otherwise specified.)

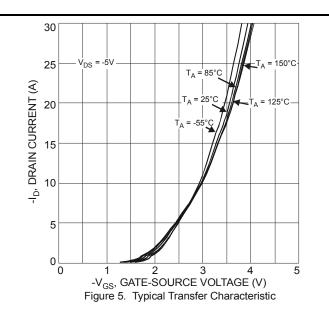
Characteristic	Symbol	Min	Тур	Max	Unit	Test	Condition
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	-40			V	I _D = -250µA, V _{GS} = 0V	
Zero Gate Voltage Drain Current	I _{DSS}	_		-1	μA	V _{DS} = -40V, V _O	_{SS} = 0V
Gate-Source Leakage	I _{GSS}	_		±100	nA	V_{GS} = ±20V, V_{DS} = 0V	
ON CHARACTERISTICS					-		
Gate Threshold Voltage	V _{GS(th)}	-0.8	-1.3	-1.8	V	I _D = -250μA, V	_{DS} = V _{GS}
Static Drain-Source On-Resistance (Note 9)	Deserver		18	25	mΩ	V _{GS} = -10V, I _D = -3A	
Static Drain-Source On-Resistance (Note 9)	R _{DS} (ON)		30	45		V _{GS} = -4.5V, I _D = -3A	
Forward Transconductance (Notes 9 & 10)	g fs	_	16.6		S	V _{DS} = -5V, I _D = -3A	
Diode Forward Voltage (Note 9)	V _{SD}	_	-0.7	-1	V	I _S = -1A, V _{GS} = 0V	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}	_	1643	—		pF $V_{DS} = -20V, V_{GS} = 0V$ f = 1MHz	
Output Capacitance	C _{oss}	_	179	—	pF		
Reverse Transfer Capacitance	Crss	_	128	—			
Gate Resistance	R _g	_	6.43	_	Ω	V_{DS} = 0V, V_{GS}	= 0V, f = 1MHz
Total Gate Charge (Note 11)	Qg	_	14	_		V _{GS} = -4.5V	
Total Gate Charge (Note 11)	Qg	_	33.7	_	nC	V _{GS} = -10V V _{DS} = -20 ^v I _D = -3A	V _{DS} = -20V
Gate-Source Charge (Note 11)	Q _{gs}	_	5.5	_			I _D = -3A
Gate-Drain Charge (Note 11)	Q _{gd}		7.3	—]		
Turn-On Delay Time (Note 11)	t _{D(on)}	_	6.9	_			
Turn-On Rise Time (Note 11)	tr	_	14.7	_	V _{DD} = -20V, V _{GS}		₆₅ = -10V
Turn-Off Delay Time (Note 11)	t _{D(off)}	_	53.7	_	ns	I _D = -3A	
Turn-Off Fall Time (Note 11)	t _f		30.9	_]		

Notes:

9. Measured under pulsed conditions. Pulse width \leq 300µs; duty cycle \leq 2%. 10. For design aid only, not subject to production testing. 11. Switching characteristics are independent of operating junction temperatures.

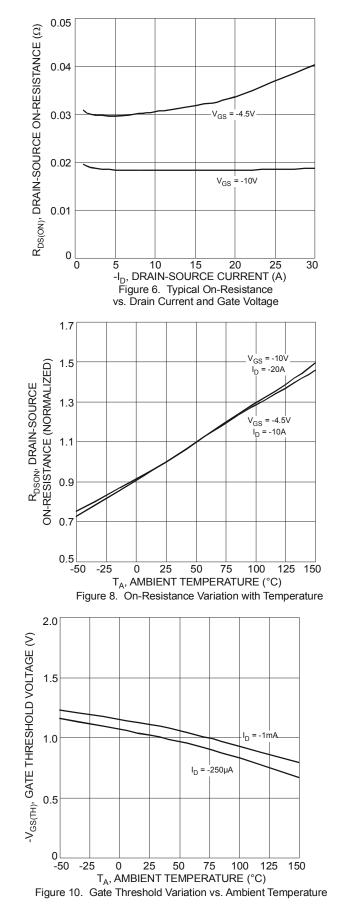
Typical Characteristics

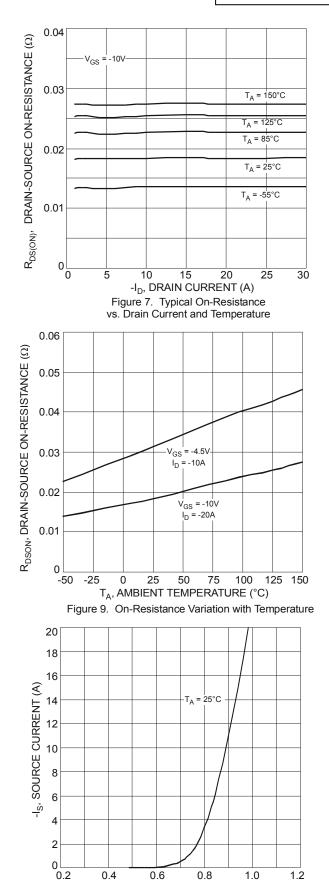






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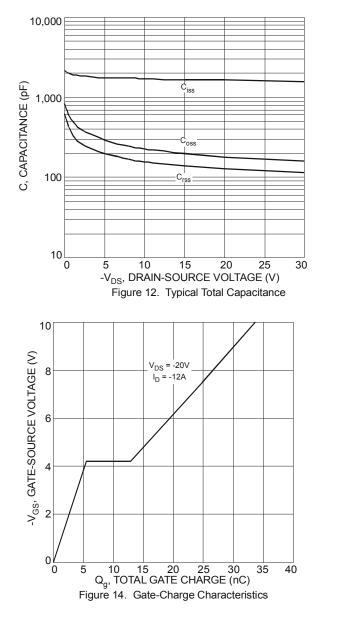


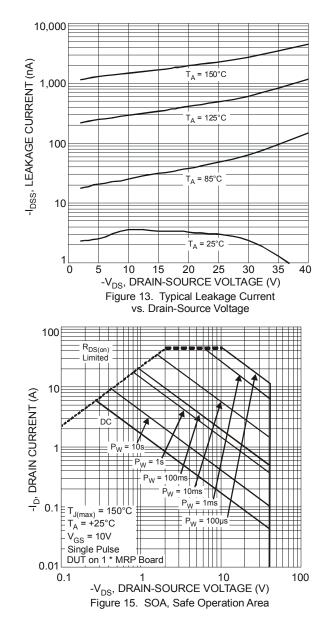


0.4 0.6 0.8 1.0 1.2 -V_{SD}, SOURCE-DRAIN VOLTAGE (V) Figure 11. Diode Forward Voltage vs. Current



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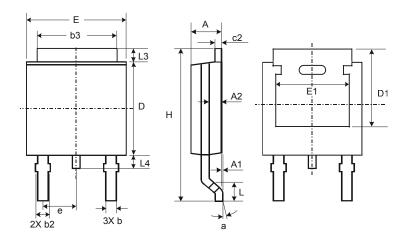






Package Outline Dimensions

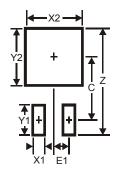
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



	TO252					
Dim	Min	Max	Тур			
Α	2.19	2.39	2.29			
A1	0.00	0.13	0.08			
A2	0.97	1.17	1.07			
b	0.64	0.88	0.783			
b2	0.76	1.14	0.95			
b3	5.21	5.46	5.33			
c2	0.45	0.58	0.531			
D	6.00	6.20	6.10			
D1	5.21	-	-			
е	-	-	2.286			
Е	6.45	6.70	6.58			
E1	4.32	-	-			
Н	9.40	10.41	9.91			
L	1.40	1.78	1.59			
L3	0.88	1.27	1.08			
L4	0.64	1.02	0.83			
а	0°	10°	_			
All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	11.6
X1	1.5
X2	7.0
Y1	2.5
Y2	7.0
С	6.9
E1	2.3



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